

2M x 8 SRAM MODULE

SYS82000FK - 020/025/35

Issue 1.2 : February 2000

Description

The SYS82000FK is a plastic 16Mbit Static RAM Module housed in a JEDEC standard 36 pin Dual In-Line package organised as 2Mx8.

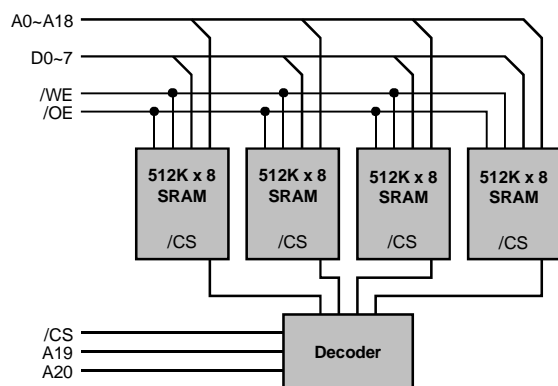
The module utilises 512Kx8 SRAM's housed in SOJ packages, and uses double sided surface mount techniques, buried decoder and dual board construction to achieve a very high density module, emulating the 16Mbit monolithic pinout.

Access times of 20 to 35 ns are available. The \overline{OE} pin allows faster access times than address access during a read cycle.

Features

- Access Times of 20/25/35 ns.
- 36 Pin JEDEC standard Dual-In-Line package.
- 5 Volt Supply $\pm 10\%$.
- Low Power Dissipation:
Average (min cycle) 2.15W (max).
Standby (-L Version CMOS) 220mW (max).
- Completely Static Operation.
- Low Voltage V_{CC} Data Retention.
- Equal Access and Cycle Times.
- On-board Supply Decoupling Capacitors.

Block Diagram



Pin Definition

A0	1	36	A20
A1	2	35	A19
A2	3	34	A18
A3	4	33	A17
A4	5	32	A16
CS	6	31	\overline{OE}
D0	7	30	D7
D1	8	29	D6
Vcc	9	28	GND
GND	10	27	Vcc
D2	11	26	D5
D3	12	25	D4
WE	13	24	A15
A5	14	23	A14
A6	15	22	A13
A7	16	21	A12
A8	17	20	A11
A9	18	19	A10

Pin Functions

Address Inputs	A0 ~ A20
Data Input/Output	D0 ~ D7
Chip Select	\overline{CS}
Write Enable	\overline{WE}
Output Enable	\overline{OE}
Power (+5V)	V_{CC}
Ground	GND

Package Details

Plastic 36 Pin 0.6" Dual-In-Line
Package.(DIP)

DC OPERATING CONDITIONS**Absolute Maximum Ratings** ⁽¹⁾

Parameter	Symbol	Min	Typ	Max	Unit
Voltage on any pin relative to V_{SS}	$V_T^{(2)}$	-0.3	-	7.0	V
Power Dissipation	P_T	-	1.0	-	W
Storage Temperature	T_{STG}	-55	-	125	°C

Notes : (1) Stresses above those listed may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

(2) V_T can be -3.0V pulse of less than 30ns.

Recommended Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit
Supply Voltage	V_{CC}	4.5	5.0	5.5	V
Input High Voltage	V_{IH}	2.2	-	$V_{CC}+0.3$	V
Input Low Voltage	V_{IL}	-0.3	-	0.8	V
Operating Temperature (Commercial)	T_A	0	-	70	°C
(Industrial)	T_{AI}	-40	-	85	°C

DC Electrical Characteristics ($V_{CC}=5V\pm10\%$) T_A 0 to 70 °C

Parameter	Symbol	Test Condition	Min	Typ	max	Unit
I/P Leakage Current Address, \overline{OE} , \overline{WE}	I_{LI}	$0V \leq V_{IN} \leq V_{CC}$	-20	-	20	μA
Output Leakage Current	I_{LO}	$\overline{CS} = V_{IH}$, $V_{I/O} = GND$ to V_{CC} , $\overline{OE} = V_{IH}$	-20	-	20	μA
Operating Supply Current	I_{CC1}	Min. Cycle, $\overline{CS} = V_{IL}$, $V_{IL} \leq V_{IN} \leq V_{IH}$	-	-	390	mA
Standby Supply Current TTL levels	I_{SB1}	$\overline{CS} = V_{IH}$	-	-	240	mA
CMOS levels	I_{SB2}	$\overline{CS} \geq V_{CC}-0.2V$, $0.2 \leq V_{IN} \leq V_{CC}-0.2V$	-	-	60	mA
Output Voltage	V_{OL}	$I_{OL} = 8.0mA$	-	-	0.4	V
	V_{OH}	$I_{OH} = -4.0mA$	2.4	-	-	V

Typical values are at $V_{CC}=5.0V$, $T_A=25^\circ C$ and specified loading.

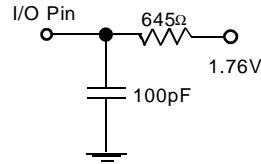
Capacitance ($V_{CC}=5V\pm10\%$, $T_A=25^\circ C$)

Note: Capacitance calculated, not measured.

Parameter	Symbol	Test Condition	max	Unit
Input Capacitance (Address, \overline{OE} , \overline{WE})	C_{IN1}	$V_{IN} = 0V$	35	pF
Input Capacitance (other)	C_{IN2}	$V_{IN} = 0V$	10	pF
I/O Capacitance	$C_{I/O}$	$V_{I/O} = 0V$	47	pF

AC Test Conditions**Output Load**

- * Input pulse levels: 0V to 3.0V
- * Input rise and fall times: 5ns
- * Input and Output timing reference levels: 1.5V
- * Output load: see diagram
- * $V_{CC}=5V\pm10\%$

**Operation Truth Table**

\overline{CS}	\overline{OE}	\overline{WE}	DATA PINS	SUPPLY CURRENT	MODE
H	X	X	High Impedance	I_{SB1}, I_{SB2}	Standby
L	L	H	Data Out	I_{CC1}	Read
L	X	L	Data In	I_{CC1}	Write
L	H	H	High-Impedance	I_{SB1}, I_{SB2}	High-Z

Notes : H = V_{IH} : L = V_{IL} : X = V_{IH} or V_{IL}

Low V_{CC} Data Retention Characteristics - L Version Only

Parameter	Symbol	Test Condition	min	typ	max	Unit
V_{CC} for Data Retention	V_{DR}	$\overline{CS} \geq V_{CC}-0.2V$	2.0	-	-	V
Data Retention Current	I_{CCDR1}	$2.0 \leq V_{CC} \leq 5.5V, \overline{CS} \geq V_{CC}-0.2$	-	-	2.4	mA
Chip Deselect to Data Retention Time	t_{CDR}	See Retention Waveform	0	-	-	ns
Operation Recovery Time	t_R	See Retention Waveform	t_{RC}	-	-	ms

Notes (1) Figures are measured over the commercial Temp range.

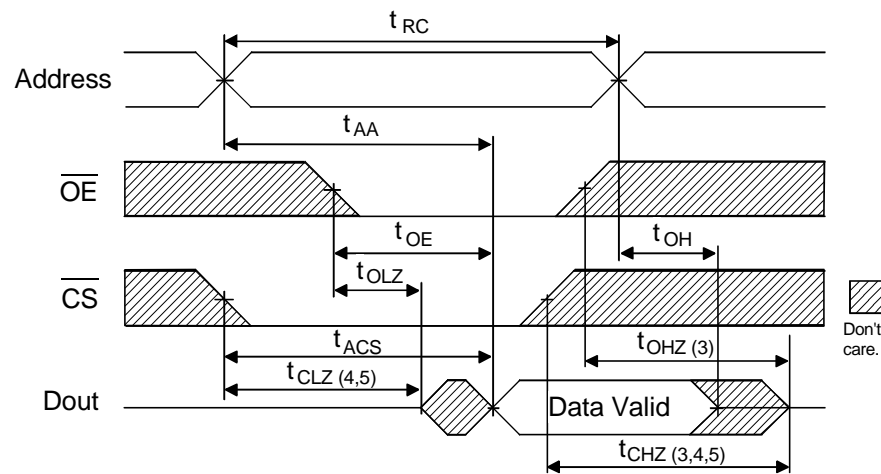
AC OPERATING CONDITIONS**Read Cycle**

Parameter	Symbol	-020		-025		-035		Unit
		min	max	min	max	min	max	
Read Cycle Time	t_{RC}	20	-	25	-	35	-	ns
Address Access Time	t_{AA}	-	20	-	25	-	35	ns
Chip Select Access Time	t_{ACS}	-	20	-	25	-	35	ns
Output Enable to Output Valid	t_{OE}	-	10	-	12	-	14	ns
Output Hold from Address Change	t_{OH}	3	-	3	-	5	-	ns
Chip Selection to Output in Low Z	t_{CLZ}	0	-	0	-	0	-	ns
Output Enable to Output in Low Z	t_{OLZ}	0	-	0	-	0	-	ns
Chip Deselection to O/P in High Z	t_{CHZ}	0	9	0	10	0	12	ns
Output Disable to Output in High Z	t_{OHZ}	0	9	0	10	0	12	ns

Write Cycle

Parameter	Symbol	-20		-25		-35		Unit
		min	max	min	max	min	max	
Write Cycle Time	t_{WC}	20	-	25	-	35	-	ns
Chip Selection to End of Write	t_{CW}	15	-	17	-	20	-	ns
Address Valid to End of Write	t_{AW}	15	-	17	-	20	-	ns
Address Setup Time	t_{AS}	0	-	0	-	0	-	ns
Write Pulse Width	t_{WP}	15	-	17	-	20	-	ns
Write Recovery Time	t_{WR}	0	-	0	-	3	-	ns
Write to Output in High Z	t_{WHZ}	0	9	0	10	0	15	ns
Data to Write Time Overlap	t_{DW}	10	-	12	-	20	-	ns
Data Hold from Write Time	t_{DH}	0	-	0	-	0	-	ns
Output active from End of Write	t_{OW}	3	-	5	-	5	-	ns

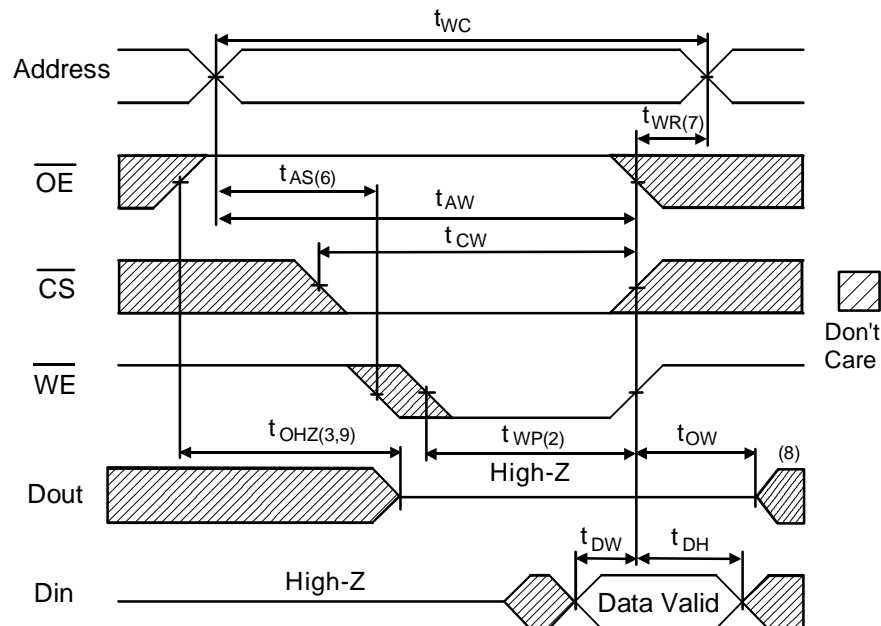
Read Cycle Timing Waveform ^(1,2)



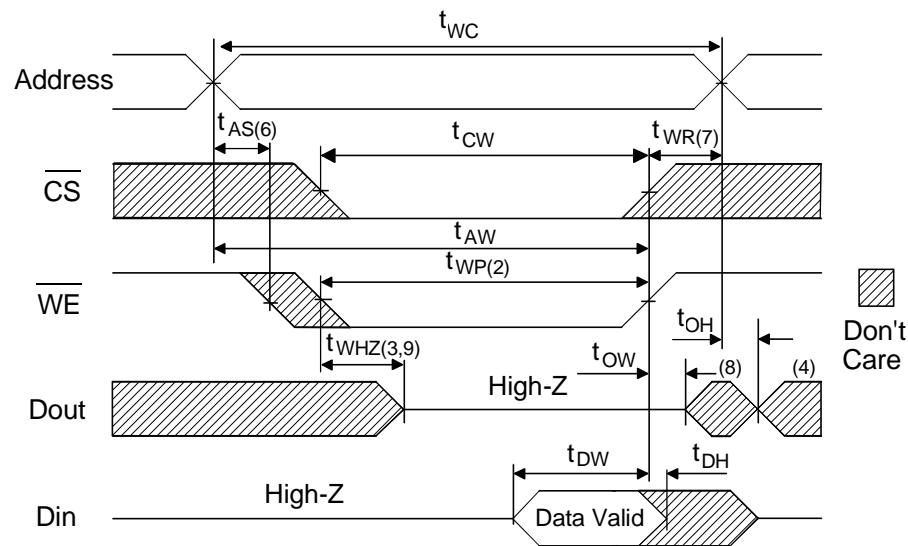
AC Read Characteristics Notes

- (1) \overline{WE} is High for Read Cycle.
- (2) All read cycle timing is referenced from the last valid address to the first transition address.
- (3) t_{CHZ} and t_{OHZ} are defined as the time at which the outputs achieve open circuit conditions and are not referenced to output voltage levels.
- (4) At any given temperature and voltage condition, t_{CHZ} (max) is less than t_{CLZ} (min) both for a given module and from module to module.
- (5) These parameters are sampled and not 100% tested.

Write Cycle No.1 Timing Waveform ^(1,4)



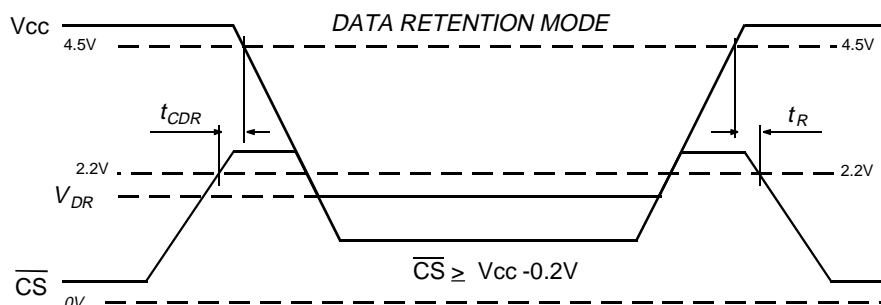
Write Cycle No.2 Timing Waveform ^(1,5)



AC Write Characteristics Notes

- (1) All write cycle timing is referenced from the last valid address to the first transition address.
- (2) All writes occur during the overlap of \overline{CS} and \overline{WE} low.
- (3) If \overline{OE} , \overline{CS} , and \overline{WE} are in the Read mode during this period, the I/O pins are low impedance state. Inputs of opposite phase to the output must not be applied because bus contention can occur.
- (4) Dout is the Read data of the new address.
- (5) \overline{OE} is continuously low.
- (6) Address is valid prior to or coincident with \overline{CS} and \overline{WE} low, too avoid inadvertant writes.
- (7) \overline{CS} or \overline{WE} must be high during address transitions.
- (8) When \overline{CS} is low : I/O pins are in the output state. Input signals of opposite phase leading to the output should not be applied.
- (9) Defined as the time at which the outputs achieve open circuit conditions and are not referenced to output voltage levels. These parameters are sampled and not 100% tested.

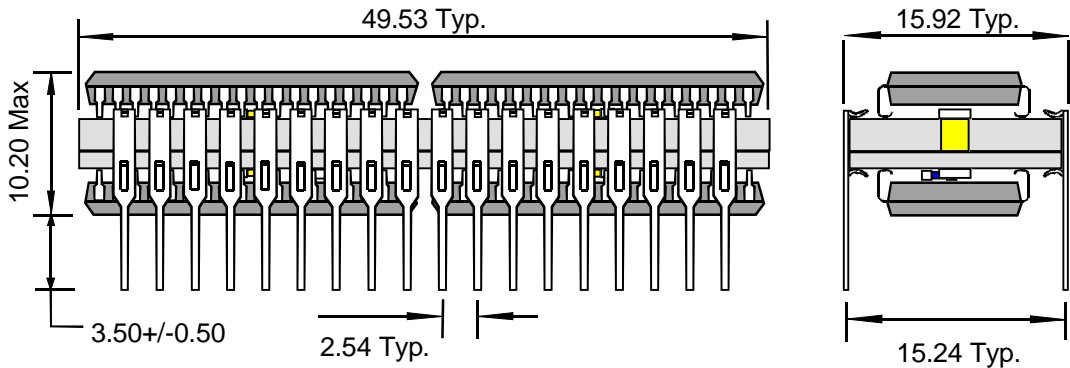
Data Retention Waveform



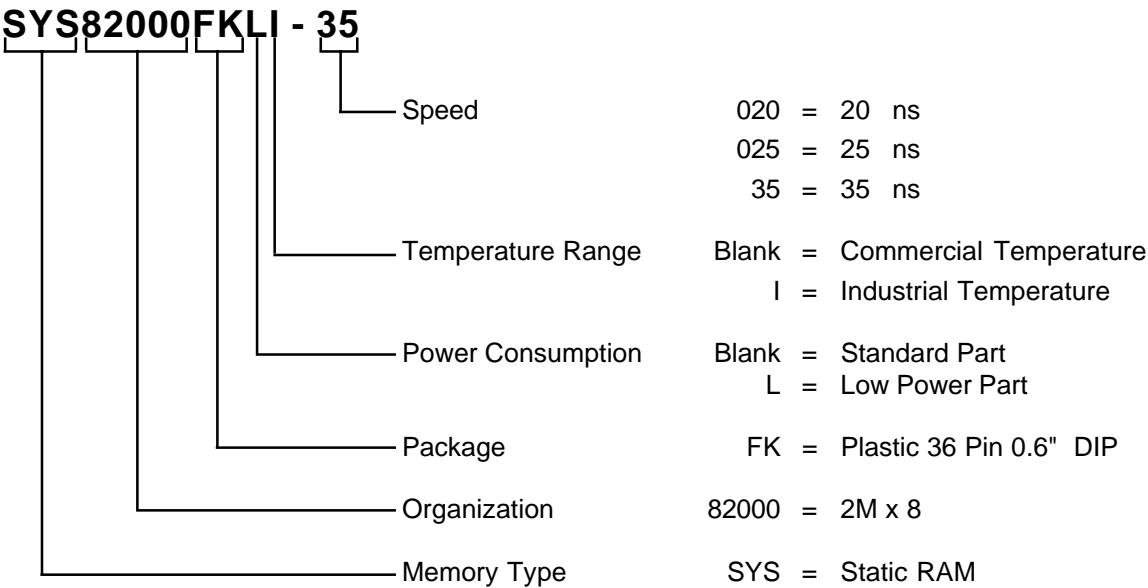
Package Information

Dimensions in mm

Plastic 36 Pin 0.6" Dual-in-Line (DIP)



Ordering Information



Note :
Although this data is believed to be accurate, the information contained herein is not intended to and does not create any warranty of merchantability or fitness for a particular purpose.
Our products are subject to a constant process of development. Data may be changed at any time without notice.
Products are not authorised for use as critical components in life support devices without the express written approval of a company director